

Oxygen isotope effects in high-quality thin films of manganites: Quantitative constraints on the physics of manganites

G. M. Zhao^(1,2), D. J. Kang⁽¹⁾, W. Prellier^(1,*), M. Rajeswari⁽¹⁾,

H. Keller⁽²⁾, T. Venkatesan⁽¹⁾ and R. L. Greene⁽¹⁾

⁽¹⁾ Center for Superconductivity Research, University of Maryland, College Park, MD 20742, USA

⁽²⁾ Physik-Institut der Universität Zürich, CH-8057 Zürich, Switzerland

Oxygen isotope effects on the transport properties have been studied in high-quality epitaxial thin films of $\text{La}_{0.75}\text{Ca}_{0.25}\text{MnO}_3$ and $\text{Nd}_{0.7}\text{Sr}_{0.3}\text{MnO}_3$. In the paramagnetic state, the resistivity can be well fitted by $\rho(T) = (A/\sqrt{T})\exp(E_p/k_B T)$ with the parameters A and E_p depending strongly on the oxygen isotope mass. The resistivity below 80 K almost perfectly follows $\rho = \rho_o + B\omega_s/\sinh^2(\hbar\omega_s/2k_B T)$ with $\hbar\omega_s/k_B \sim 100$ K. Both ρ_o and B increase by about 15(3)% upon replacing ^{16}O by ^{18}O . The results provide quantitative constraints on the basic physics of manganites.

The discovery of “colossal” magnetoresistance (CMR) in thin films of $\text{Re}_{1-x}\text{A}_x\text{MnO}_3$ (Re = a rare-earth element, and A = a divalent element) [1] has stimulated extensive studies of magnetic, structural and transport properties of these materials [2]. The physics of manganites has primarily been described by the double-exchange (DE) model [3]. However, Millis, Littlewood and Shraiman [4] pointed out that the carrier-spin interaction in the DE model is too weak to lead to the carrier localization in the paramagnetic state, and thus a second mechanism such as small polaronic effects should be involved to explain the observed resistivity data in doped manganites. The central point of the model is that in the paramagnetic state the electron-phonon coupling constant λ is large enough to form small polarons while the growing ferromagnetic order increases the bandwidth and thus decreases λ sufficiently to form a large polaron metallic state. Many recent experiments [8–14] have provided strong evidence for the existence of small polarons in the paramagnetic state, and qualitatively support these theoretical models [4–6].

Alexandrov and Bratkovsky [7] have recently argued that the model suggested by Millis *et al.*, cannot quantitatively explain CMR since the characteristic theoretical field (~ 15 T) for CMR is too high compared with the experimental one (~ 4 T) [4]. They thus proposed an alternative theory for CMR. The basic idea of their model is that the small polarons form localized bound pairs (bipolarons) in the paramagnetic state due to strong electron-phonon coupling while the competing exchange interaction of polaronic carriers with localized spins drives the ferromagnetic transition. The transition is accompanied by a giant increase in the number of small polarons which are mobile carriers and move coherently at low temperatures. This model appears to be able to explain the CMR quantitatively.

In order to discriminate between these different mod-

els, we study the oxygen isotope effect on the transport properties of high-quality epitaxial thin films of $\text{La}_{0.75}\text{Ca}_{0.25}\text{MnO}_3$ and $\text{Nd}_{0.7}\text{Sr}_{0.3}\text{MnO}_3$. The intrinsic resistivity of these compounds shows a strong dependence on the oxygen isotope mass in both paramagnetic and ferromagnetic states. A quantitative data analysis provides essential constraints on the basic physics of manganites.

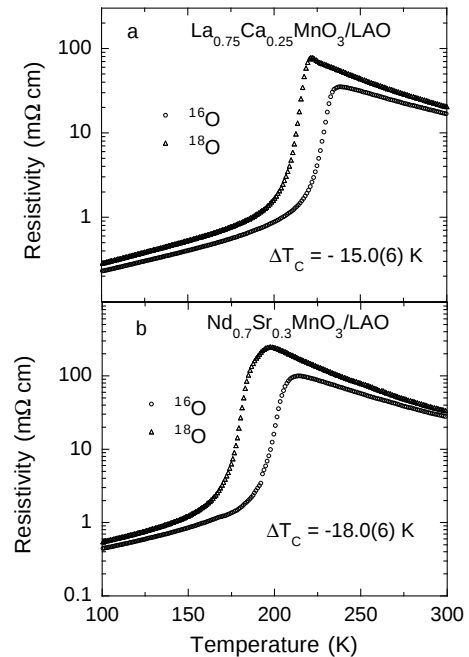


FIG. 1. The resistivity of the oxygen-isotope exchanged films of (a) $\text{La}_{0.75}\text{Ca}_{0.25}\text{MnO}_3$; (b) $\text{Nd}_{0.7}\text{Sr}_{0.3}\text{MnO}_3$.

The epitaxial thin films of $\text{La}_{0.75}\text{Ca}_{0.25}\text{MnO}_3$ (LCMO) and $\text{Nd}_{0.7}\text{Sr}_{0.3}\text{MnO}_3$ (NSMO) were grown on $\langle 100 \rangle$ LaAlO_3 single crystal substrates by pulsed laser depo-

sition using a KrF excimer laser [15]. The film thickness was about 190 nm for NSMO and 150 nm for LCMO. Two halves were cut from the same piece of a film for oxygen-isotope diffusion. The diffusion for LCMO/NSMO was carried out for 10 h at about 940/900 °C and oxygen pressure of about 1 bar. The ^{18}O -isotope gas is enriched with 95% ^{18}O , which can ensure 95% ^{18}O in the ^{18}O thin films. The resistivity was measured using the van der Pauw technique, and the contacts were made by silver paste. The measurements were carried out from 5 to 380 K in a Quantum Design measuring system.

Fig. 1 shows the resistivity of the oxygen-isotope exchanged films of (a) LCMO; (b) NSMO over a temperature range 100-300 K. It is striking that, in all the cases, the ^{18}O samples have lower metal-insulator crossover temperatures and much sharper resistivity drop. The Curie temperature T_C normally coincides with a temperature where $d \ln \rho / dT$ exhibits a maximum. We find that the oxygen isotope shift of T_C is 15.0(6) K for LCMO, and 18.0(6) K for NSMO, in excellent agreement with the results for the bulk samples [16].

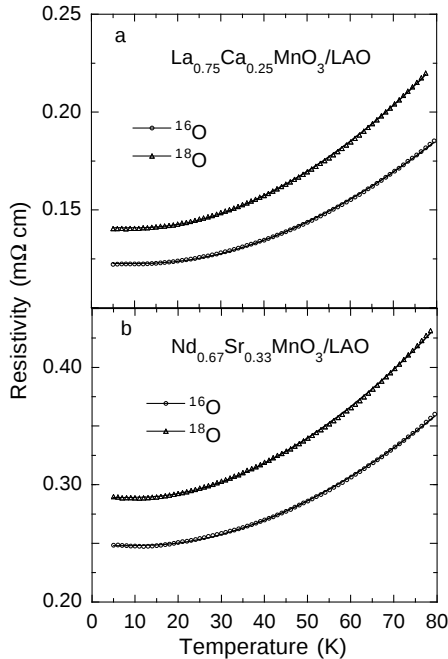


FIG. 2. The low-temperature resistivity of the oxygen-isotope exchanged films of (a) $\text{La}_{0.75}\text{Ca}_{0.25}\text{MnO}_3$; (b) $\text{Nd}_{0.67}\text{Sr}_{0.33}\text{MnO}_3$. The solid lines are fitted curves by Eq. 1.

In Fig. 2 we plot the low-temperature resistivity of the oxygen-isotope exchanged films of (a) LCMO; (b) NSMO. In both cases, the residual resistivity ρ_0 for the ^{18}O samples is larger than for the ^{16}O samples by about 15%. We have repeated the van der Pauw measurements at 5 K for several times with different contact configurations. We checked that the uncertainty of the difference in ρ_0 of the two isotope samples is less than 3%. We

also found that the isotope effect is reversible upon the isotope back-exchange. It is worth noting that the ρ_0 for the ^{16}O NSMO film is nearly the same as for a single crystalline sample [17]. This indicates that the electrical transport properties observed in our films are intrinsic.

The low temperature resistivity has been explained by small polaron metallic conduction [18], which leads to a formula [18,19]:

$$\rho(T) = \rho_0 + B\omega_s / \sinh^2(\hbar\omega_s/2k_B T), \quad (1)$$

where ω_s is the frequency of the softest optical mode (about 100 K [18]), and B is a constant, being proportional to m_p/n (here m_p is the effective mass of polarons, and n is the mobile carrier concentration). The residual resistivity $\rho_0 \propto m_p/n\tau_0$ [20], where $\hbar/\tau_0$ is the zero temperature scattering rate which is associated with the random potential produced by randomly distributed trivalent and divalent cations [21]. The magnitude of $\hbar/\tau_0$ has been found to be 18(3) meV from optical data of the compounds $\text{Nd}_{0.7}\text{Sr}_{0.3}\text{MnO}_3$ [17], $\text{La}_{0.7}\text{Sr}_{0.3}\text{MnO}_3$ and $\text{La}_{0.7}\text{Ca}_{0.3}\text{MnO}_3$ [22]. Since the Drude weight ($\propto n/m_p$) for $\text{Nd}_{0.7}\text{Sr}_{0.3}\text{MnO}_3$ [17] is about a factor of 3 smaller than for $\text{La}_{0.7}\text{Ca}_{0.3}\text{MnO}_3$ [22], nearly the same $\hbar/\tau_0$ observed for both compounds implies that the $\hbar/\tau_0$ is nearly independent of m_p/n , and that both ρ_0 and B are proportional to m_p/n .

The best fit to the data shown in Fig. 2 indeed demonstrates that, in both cases, ρ_0 increases by 15(3)%, and B by 18(3). The results indicate that there is a substantial oxygen isotope effect on m_p/n . Since we have shown that [10,16] the total hole concentrations for two isotope samples should be the same, the observed isotope effect on m_p/n implies that m_p depends strongly on the isotope mass. This strongly suggests that the carriers in the ferromagnetic state are indeed small polarons, in agreement with the theoretical model [7]. We also find that both ρ_0 and B for NSMO are about twice as large as those for LCMO, implying that the effective mass of carriers for NSMO is larger by a factor of 2.4 than for LCMO. This is consistent with specific heat data; the electronic specific heat coefficient $\gamma \sim 8$ mJ/moleK² for $\text{La}_{0.8}\text{Ca}_{0.2}\text{MnO}_3$ [23], while $\gamma \sim 20$ mJ/moleK² for $\text{Nd}_{0.67}\text{Sr}_{0.33}\text{MnO}_3$ [24].

In the paramagnetic state, the dominant conduction mechanism is thermally activated hopping of adiabatic small polarons. The mobility is given by [25]

$$\mu = \frac{ed^2}{h} \frac{\hbar\omega_o}{k_B T} \exp(-E_a/k_B T), \quad (2)$$

where d is the site to site hopping distance, which is equal to $a/\sqrt{2}$ since the carriers in manganites mainly reside on the oxygen sites [26], ω_o is the characteristic frequency of the optical phonons, and E_a is given by [27,25,28] $E_a = (\eta E_p/2)f(T) - t$, where E_p is the polaron binding energy, t is the “bare” hopping integral, η is a constant ($\eta = 1$ for Holstein polarons [25] and $\eta \sim 0.2-0.4$ for Fröhlich polarons [29]), and $f(T) = [\tanh(\hbar\omega_o/4k_B T)]/(\hbar\omega_o/4k_B T)$ [27].

If one considers that small polarons can be bound into localized pairs (bipolarons) [7] or to the impurity centers [20], one finds [7,20] that the mobile carrier density $n = 2(2\pi m_p k_B T / \hbar^2)^{3/2} \exp(-\Delta/2k_B T)$ when $T < W_p/k_B$ and for a parabolic band, where W_p is the polaron bandwidth ($m_p = 6\hbar^2/a^2 W_p$), Δ is the bipolaron binding energy [7] or twice the gap between localized impurity levels and the bottom of the polaron band [20]. In fact, the above $n(T)$ expression is the same as that for semiconductors when the chemical potential is pinned to the mobility edge of the bipolarons or to the impurity levels. For a single-type (hole or electron) carrier system, $\Delta = 2E_s$, where E_s is the activation energy deduced from thermopower data. Then in the temperature region: $T_C < T < W_p/k_B$, the resistivity $\rho = 1/ne\mu$ is given by

$$\rho = \frac{A}{\sqrt{T}} \exp(E_p/k_B T), \quad (3)$$

where $A = (ah/e^2\sqrt{k_B})(1.05W_p)^{1.5}/\hbar\omega_o$, and $E_p = E_a + \Delta/2$. The quantity A should strongly depend on the isotope mass because $W_p = W_o \exp(-\Gamma E_p/\hbar\omega_o) = W_o \exp(-g^2)$. Here W_o is the bare bandwidth ($W_o = 12t$), Γ is a constant, which is less than 0.4 for both Holstein and Fröhlich polarons when the coupling constant $\lambda = 2E_p/W_o < 0.5$ and $\hbar\omega_o/t < 1$ [30]. For $T \gg W_p/k_B$, the exponential prefactor in Eq. 3 will be proportional to T/ω_o [8]. In this case, the exponent of the isotope effect on the prefactor is about -0.5, in sharp contrast to a large and positive exponent predicted by Eq. 3.

In Fig. 3, we show the resistivity in the paramagnetic state for the ^{16}O and ^{18}O films of (a) LCMO; (b) NSMO. It is clear that the resistivity strongly depends on the oxygen isotope mass. The data can be well fitted by Eq. 3 with the parameters: $A = 17.3/12.7 \text{ m}\Omega\text{cm K}^{0.5}$, $E_p/k_B = 844.3/997.2 \text{ K}$ for the LCMO $^{16}\text{O}/^{18}\text{O}$ film; $A = 22.2/16.2 \text{ m}\Omega\text{cm K}^{0.5}$, $E_p/k_B = 925/1082 \text{ K}$ for the NSMO $^{16}\text{O}/^{18}\text{O}$ film. For LCMO, the parameter A decreases by 35(5)%, and E_p increases by 13.2(5) meV. For NSMO, A decreases by 37(8)%, and E_p increases by 13.5(9) meV. The observed large oxygen isotope effect on the parameter A is consistent with Eq. 3. It is worth noting that since the activation energy is large, one can also fit the data by $\rho(T) = AT^\beta \exp(E_p/k_B T)$ with β varying from -2 to 2.

We can use the values of the parameter A for the ^{16}O films to calculate the polaron bandwidth W_p according to the relation: $A = (ah/e^2\sqrt{k_B})(1.05W_p)^{1.5}/\hbar\omega_o$. By taking $\hbar\omega_o = 74 \text{ meV}$, typical for oxides [30], we yield $W_p = 49 \text{ meV}$ for the LCMO ^{16}O film, and 58 meV for the NSMO ^{16}O film. The polaron bandwidth is greatly reduced compared with the bare bandwidth W_o , which can be estimated to about 4.9 eV from the relation: $W_o = 6\hbar^2/a^2 m_b$ and $m_b = 0.61m_e$ [18]. Then we can determine g^2 to be 4.61/4.44 for the LCMO/NSMO ^{16}O film using $g^2 = \ln(W_o/W_p)$. If $\hbar\omega_o$ decreases by 5.7% upon replacing ^{16}O by ^{18}O , then our calculation shows

that the parameter A decreases by 35% for LCMO, and by 33% for the NSMO, in good agreement with the measured values: 35(5)% for LCMO and 37(8)% for NSMO.

It is important to clarify whether the small polarons are bound into localized pairs (bipolarons) or just to the impurity centers since this can place an essential experimental constraint on various CMR theories. If the small polarons are bound to the impurity centers, there will be no isotope effect on Δ [20]. In this case, the isotope effect on E_p only arises from the isotope shift of E_a , as seen from the relation: $E_p = E_a + \Delta/2$. Since $E_a = (\eta E_p/2)f(T) - W_o/12$, only the quantity $f(T) = [\tanh(\hbar\omega_o/4k_B T)]/(\hbar\omega_o/4k_B T)$ may depend on the isotope mass if the temperature is not so high compared with $\hbar\omega_o/k_B$. If we take $\hbar\omega_o = 74 \text{ meV}$, we have $f(T) = 0.855$ and $\delta f(T) = 0.0134$ for $T = 300 \text{ K}$, where δ means a change due to the oxygen isotope substitution. Using the relation: $(\eta E_p/2)f(T) = W_o/12 + E_p - \Delta/2$, and $\Delta/2 = E_s = 15 \text{ meV}$ for $\text{La}_{0.75}\text{Ca}_{0.25}\text{MnO}_3$ [31], we yield $\eta E_p/2 = 0.54 \text{ eV}$. Then $\delta E_p = \delta E_a = (\eta E_p/2)\delta f(T) = 7.2 \text{ meV}$, which is about half the value observed.

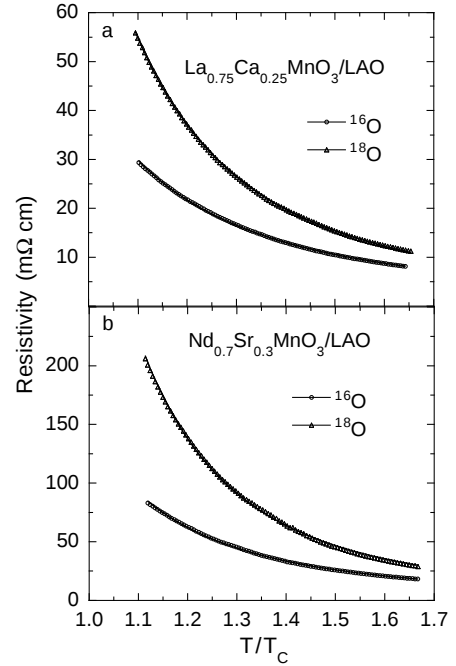


FIG. 3. The resistivity in the paramagnetic state for the ^{16}O and ^{18}O films of (a) $\text{La}_{0.75}\text{Ca}_{0.25}\text{MnO}_3$; (b) $\text{Nd}_{0.7}\text{Sr}_{0.3}\text{MnO}_3$. The solid lines are the fitted curves by Eq. 3. Note that the fit is not so perfect for the NSMO ^{18}O film since the data are not very smooth around $T = 1.4T_C$.

On the other hand, one can quantitatively explain the isotope dependence of E_p if small polarons form localized bipolarons. In this scenario, $\delta\Delta = -\delta W_p$ [29], so $\delta\Delta = 0.057g^2W_p$. From the deduced values for g^2 and W_p above, we calculate that $\delta\Delta = 12.9 \text{ meV}$ for LCMO, and 14.7 meV for NSMO. Then $\delta E_p = \delta E_a + \delta\Delta/2 =$

13.6 meV for LCMO, and 14.5 meV for NSMO. The calculated values are in excellent agreement with the observed values: 13.2(5) meV for LCMO and 13.5(9) meV for NSMO. In addition, if the small polarons are bound into small bipolarons, there will be a maximum in optical conductivity at the energy $\nu_b = 2g^2\hbar\omega_o + W_p + \Delta$ [29]. Substituting $g^2 = 4.61$, $\hbar\omega_o = 74$ meV, $W_p = 49$ meV and $\Delta = 30$ meV for the LCMO ^{16}O film, we obtain $\nu_b = 0.76$ eV, in excellent agreement with experimental results (i.e., $\nu_b \simeq 0.70$ eV for $x = 0.3$, and 0.80 eV for $x = 0.1$) [32].

In summary, the oxygen isotope effects observed in high-quality epitaxial thin films of $\text{La}_{0.75}\text{Ca}_{0.25}\text{MnO}_3$ and $\text{Nd}_{0.7}\text{Sr}_{0.3}\text{MnO}_3$ can be quantitatively explained by a scenario [7] where the small polarons form localized bound pairs (bipolarons) in the paramagnetic state while the carriers in the ferromagnetic states are small polarons due to the competing exchange interaction of polaronic carriers with localized spins. The electron-phonon coupling strength g^2 in the paramagnetic state is about twice of that in the low temperature ferromagnetic state. This is possibly because a strong screening effect by mobile charge carriers reduces the electron-phonon interaction in the ferromagnetic state. The present results provide quantitative constraints on the basic physics of manganites.

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* Present address: Laboratoire CRISMAT-ISMRA, 14050 CAEN Cedex, France.

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